



WIR SCHAFFEN WISSEN – HEUTE FÜR MORGEN

Monica Kosa :: Multiscale Materials Modelling Group, PSI, CH

Extended defects modelling of functional oxides *the intriguing case of UO_2*

Empa Postdocs-II & PSI-FELLOW II-3i RETREAT 2018

Functional Oxides in Emerging Technologies



**Li-ion Battery
Cathodes**

**All-Oxide
Photovoltaics
Light
absorbers
Charge
conductors**

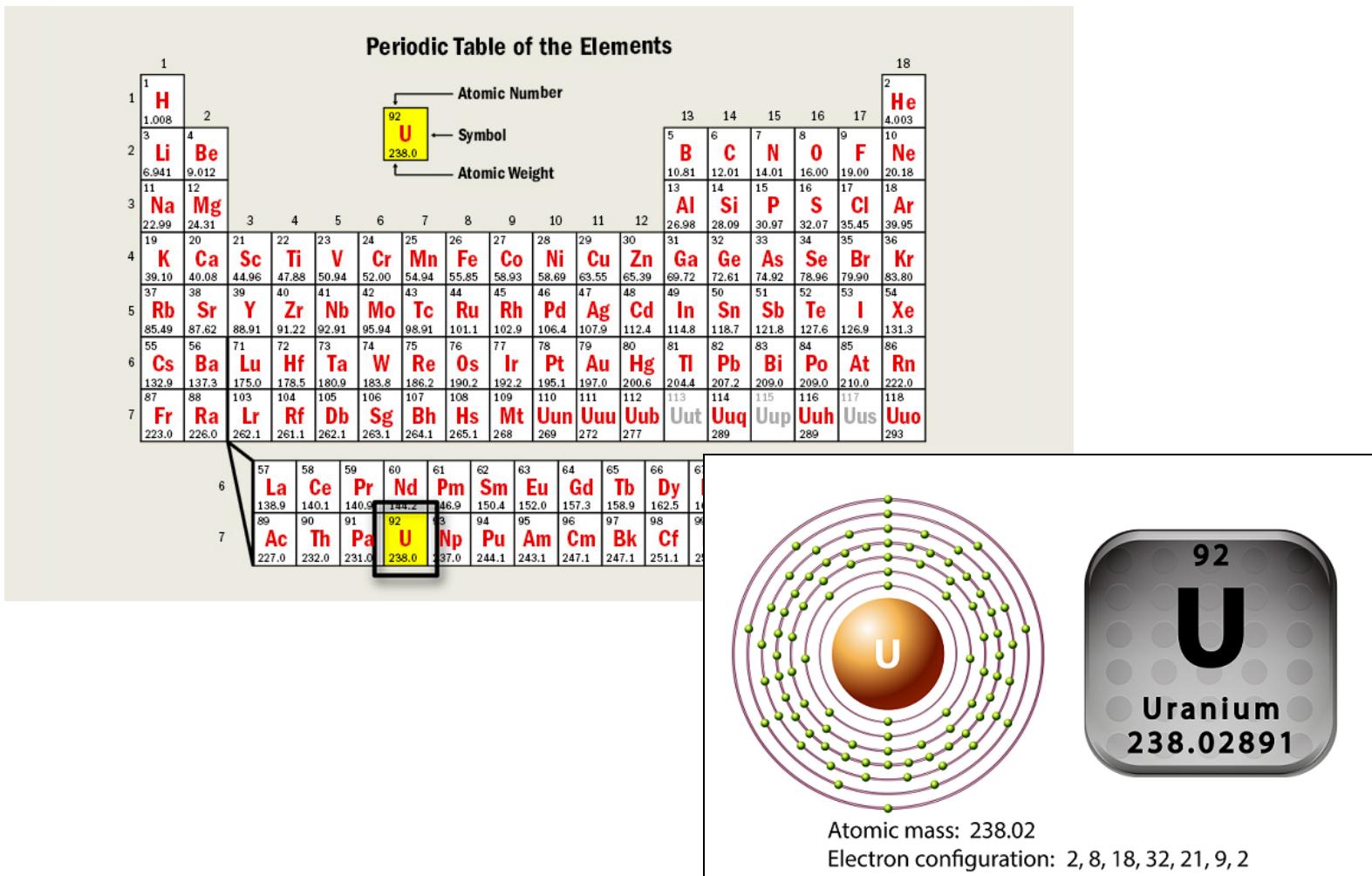
**Fuel Cells
Non precious
metal electro
catalysts**

**Nuclear Fuels
safety, UO_2**

Unifying Motif: complex electronic structure enables functionality

Practical Utilization: how MATERIALS respond to stress?

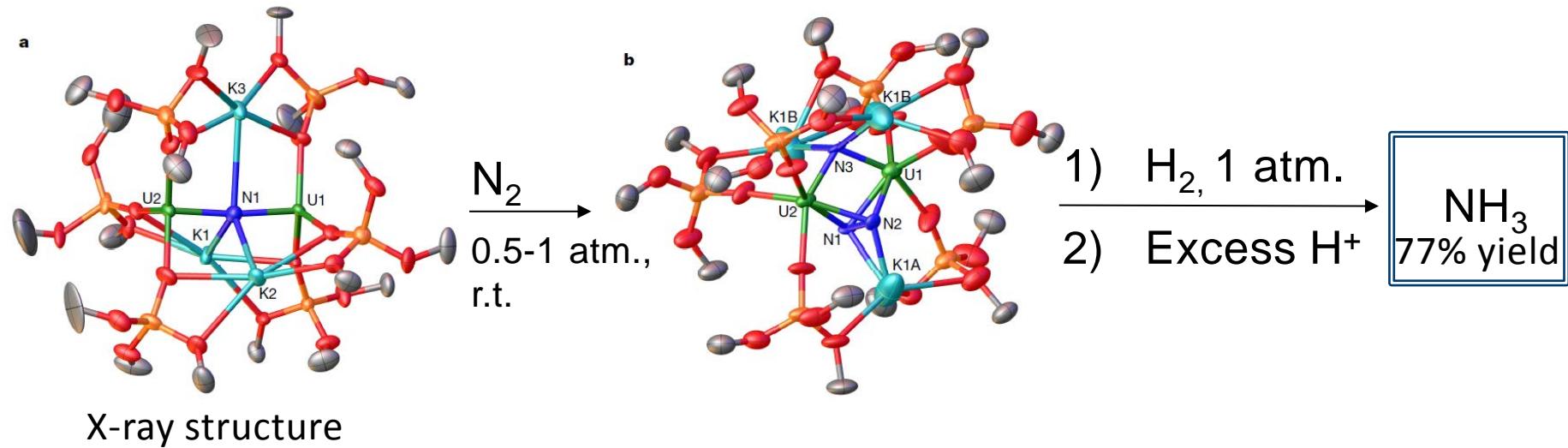
Functional Oxides – Complex Electronic Structure, UO_2 nuclear fuel



Versatility of Uranium based materials

a catalyst for N₂ Functionalization

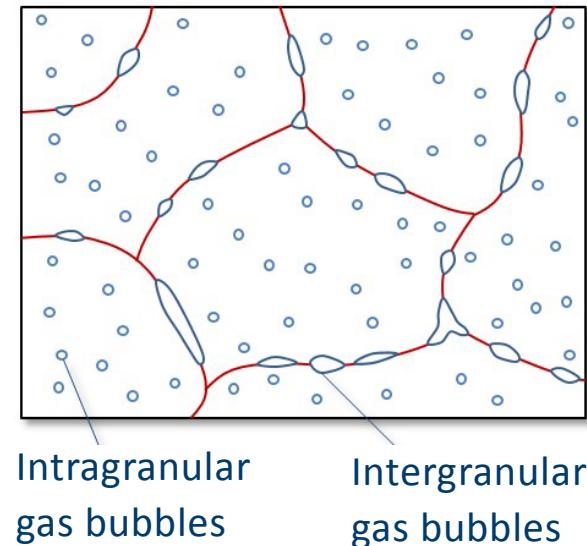
- Industrial Haber–Bosch process: $N_2 + 3H_2 \rightarrow 2NH_3$
450°C, 300 bar.
- Biological N₂ fixation, $N_2 + 8 H^+ + 8 e^- \rightarrow 2 NH_3 + H_2$



Nuclear Fuel UO_2

Mechanical Properties in the Plastic Regime

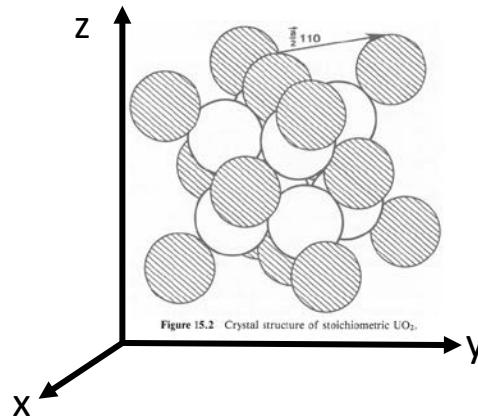
- Irradiation:
compositional changes
temperature jumps
- U fission process:
noble gases, Xe, Kr, release
insoluble in the fuel matrix
precipitate within the fuel body.
- Extended defects:
dislocations/grain boundaries can pin
and immobilize gas bubbles < 1 micron.



Structure - Property relationship of Dislocations in UO_2

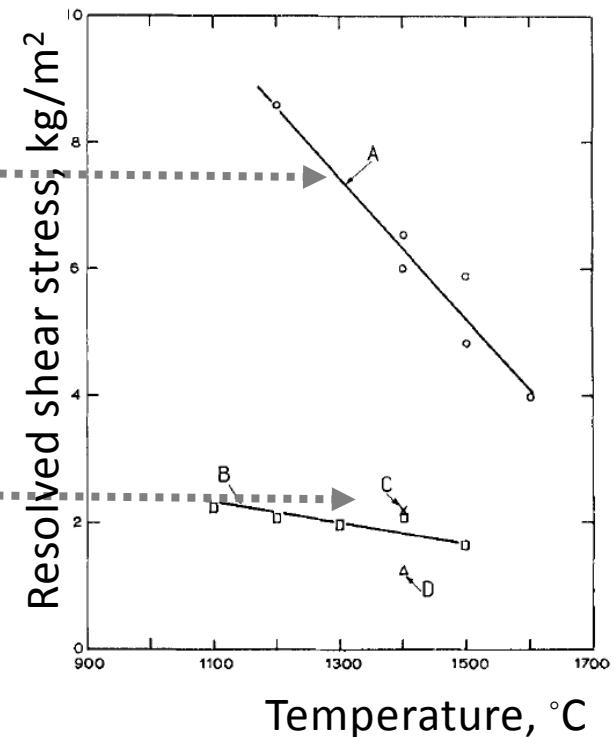
I. Experimental characterization of slip systems in UO₂, compression tests

Stoichiometric UO₂ slip systems



A difficult slip system:
 $\{110\}<110>$ (A)

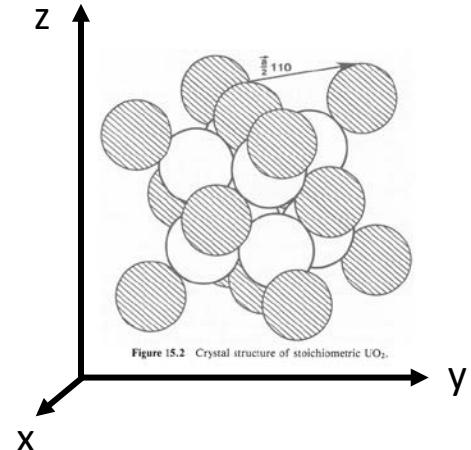
An easy slip system:
 $\{001\}<110>$ (C)



II. Experimental characterization of slip systems in UO_2 compression tests

Stoichiometric UO_2 ($\text{U}/\text{O}=2.0001$) at 873K and 523K:

A primary slip system: $\{111\}<1-10>^*$
with presence of $\{001\}<1-10>$



The reason for the dominance of $\{111\}$ slip for $T < 873 \text{ K}$ is not well understood. It was demon-

Why this behavior should be observed in UO_2 , but not in CaF_2 , is not clear; we speculate that differences in details of the bonding between anions and cations (the amount of ionic vs covalent character) may be responsible.

*50% difference in yield stresses w.r.t previous experimental studies.

Exp. characterization of $\{111\}$ slip systems using slip traces and TEM analysis: R. J. Keller, T. E. Mitchell, A. H. Heuer, *Acta Metall.*, **1988**, 36, 1061-1071.

A. H. Heuer, R. J. Keller, T. E. Mitchell in *Deformation Processes in Minerals, Ceramic and Rocks*, **1990**, Ch. 15, pp. 377-390.

The Goal and the Tasks

Understand how fission product gases interact with dislocations



Understand structure property relationship of dislocation



Develop computational tools for modelling dislocations
of materials with complex electronic structure

Empirical Potentials - Force fields

$$U(\vec{R}) = \underbrace{\sum_{bonds} k_i^{bond} (r_i - r_0)^2}_{U_{bond}} + \underbrace{\sum_{angles} k_i^{angle} (\theta_i - \theta_0)^2}_{U_{angle}} + \dots$$

Cheap computationally: Systems of 10,000-100,000 atoms.

Neglect electronic structure: Covalence in the U-O bond and change in the oxidation state.

First principles methods: DFT+U

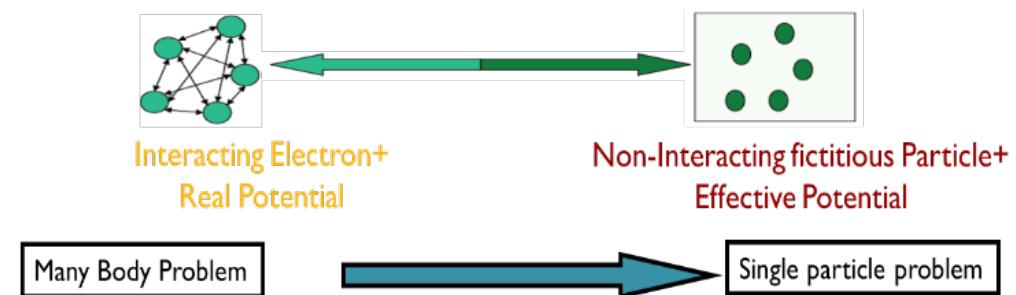
CPU intensive: 600-3000 atoms

Detailed electronic structure: bond formation, possible change in the oxidation state during dislocations.

$$\hat{H}\psi = E\psi$$

If we can solve this equation,
we know everything about
the system





Density Functional Theory modelling of UO_2

f-electrons in a standard DFT:



- dispersed among all f orbitals

f-electrons via *f orbital Occupation Pattern, FOP:*

- restoring the band gap of UO_2
- magnetic structure

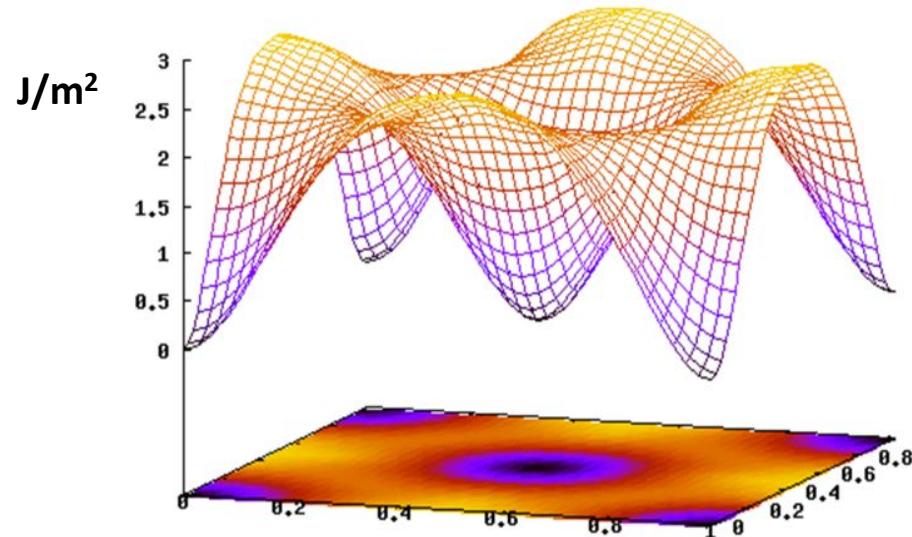


- f orbitals' localized electrons

Computational studies of dislocations in UO_2

general computational scheme

Plotting energy of crystal as function of displacement

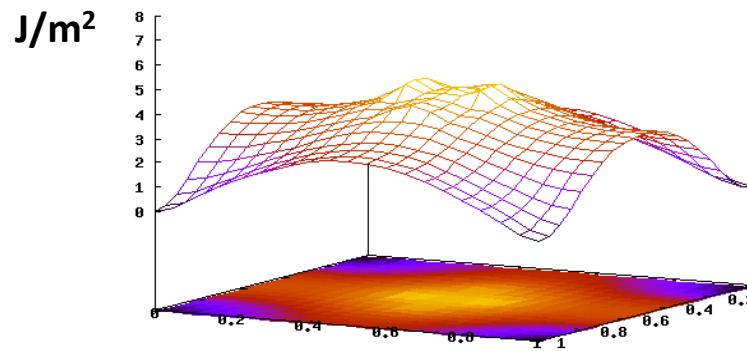


γ -surface, Generalised Stacking Fault Energies

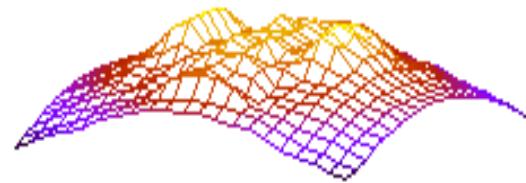
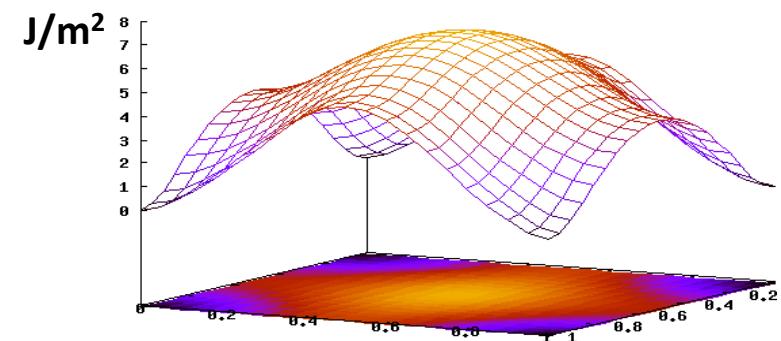
Validating Empirical Potentials with DFT+U

{110}

PBE+U



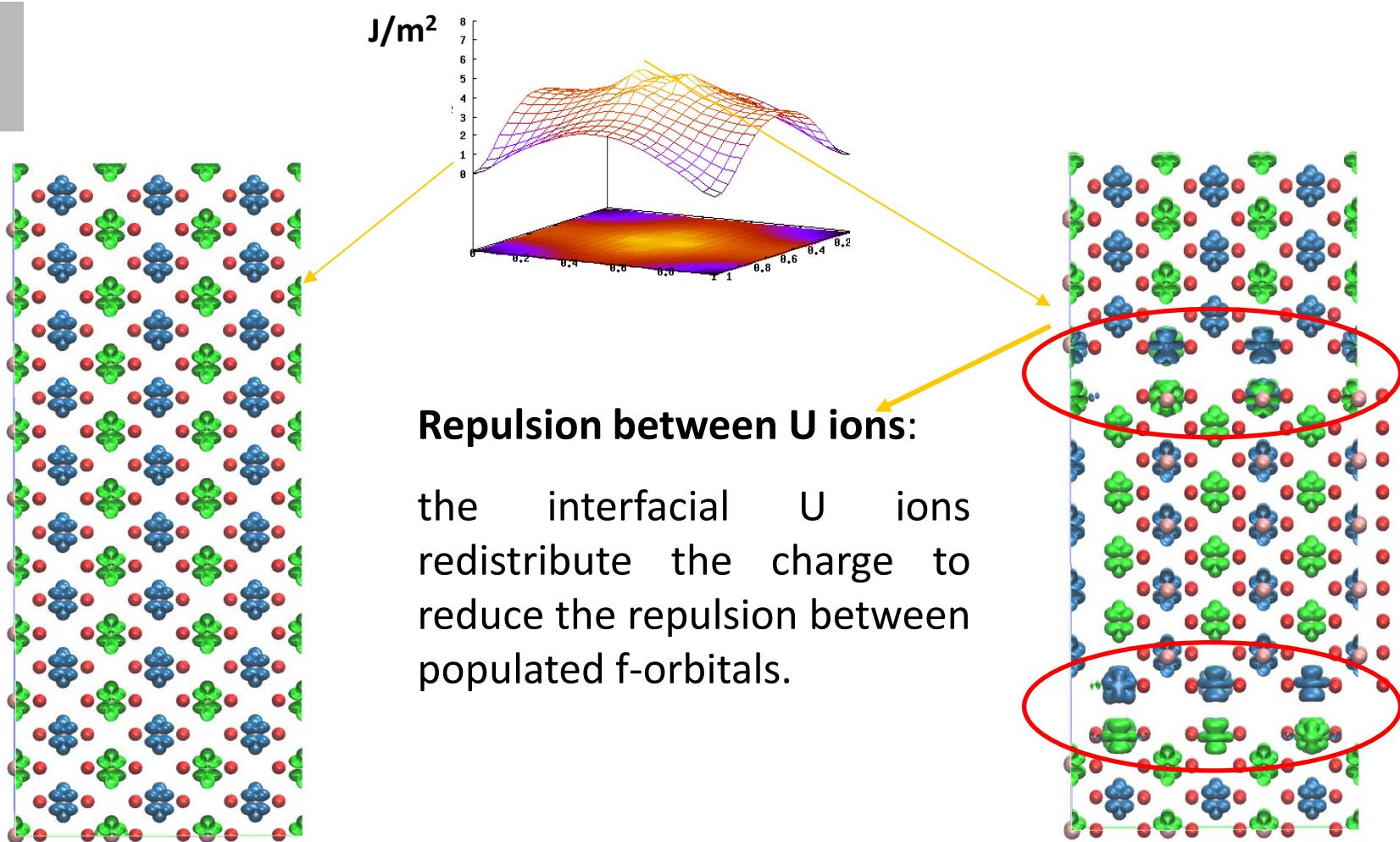
Force Field, Yakub



Fine grid of the 0.25-0.75 region
convergence w.r.t z axis

Why the DFT+U γ -surface is corrugated?

Electronic structure evolution during the {110} sampling

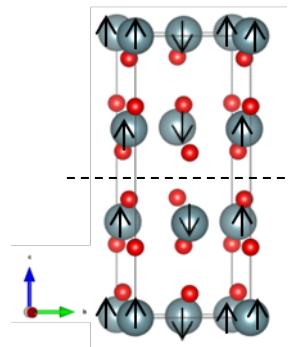


Validating Empirical Potentials with DFT+U

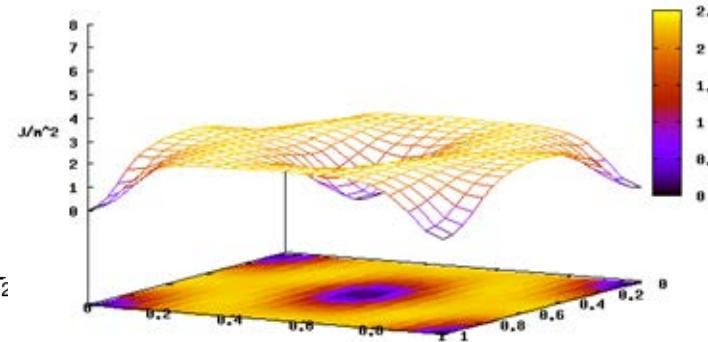
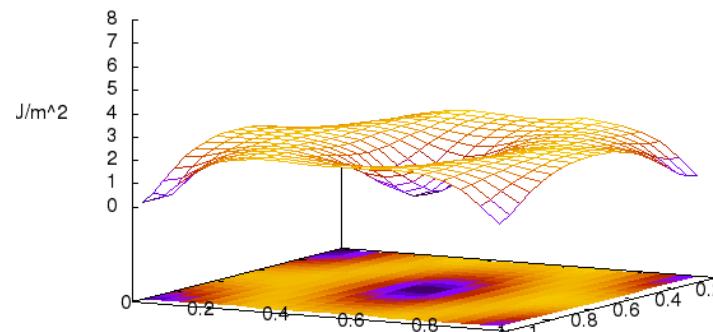
{111}

PBE+U

Force Field (Yakub)



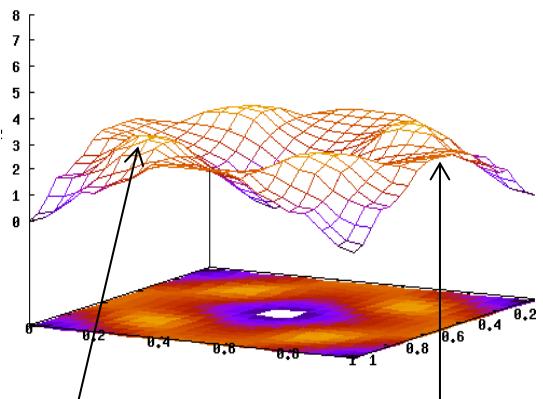
4x3x12 cell
2592 atoms (!)



- Qualitative and quantitative agreement between DFT+U and Empirical Potentials.
- The glide is governed by distortion of weak O-O interactions.

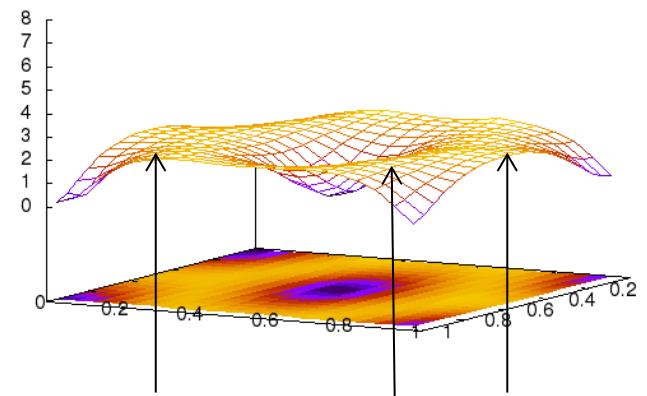
{001} and {111} lowest energy glides

{001}



2.75-3.09 J/m² **2.27-2.65 J/m²**

{111}

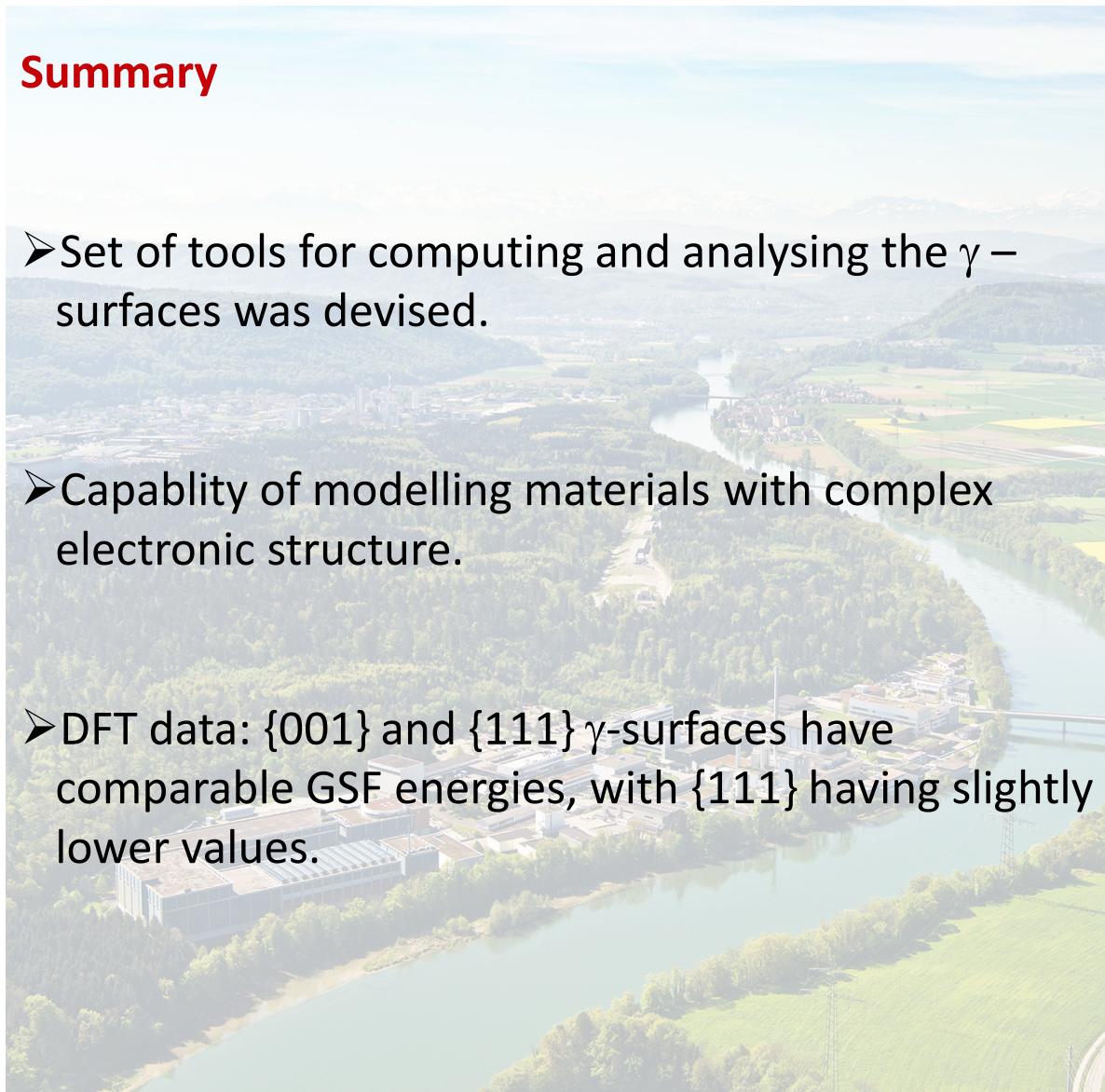


2.26-2.38 J/m² **2.24 J/m²**
2.23-2.24 J/m²

- {111} and {001} planes have comparable GSF energies, with {111} being slightly lower.
- The spread of DFT computed GSF energies: ~0.3 J/m², *f-orbital population scheme*.
- The spread of EP computed GSF energies: ~3 J/m².

Summary

- Set of tools for computing and analysing the γ – surfaces was devised.
- Capability of modelling materials with complex electronic structure.
- DFT data: {001} and {111} γ -surfaces have comparable GSF energies, with {111} having slightly lower values.



My thanks go to

- Dr. Matthias Krack, PSI, CH
- Dr. Raoul Ngayam Happy, PSI, CH
- Dr. Sébastien Groh, UniBas, CH



**HORIZON2020 COFUND:
grant agreement no. 701647
INSPYRE
CSCS**

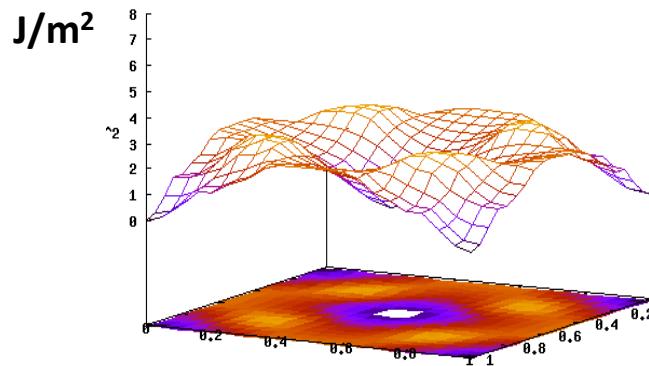
**Thank you very much
for your kind attention!**



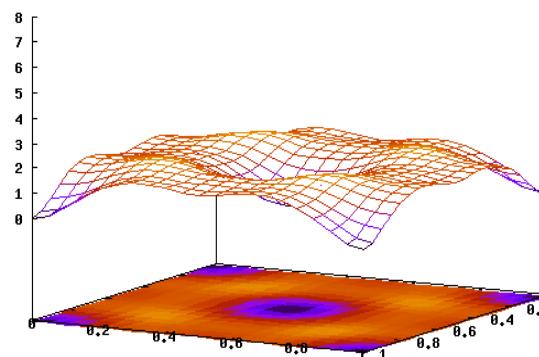
Validating Empirical Potentials with DFT+U

{001}

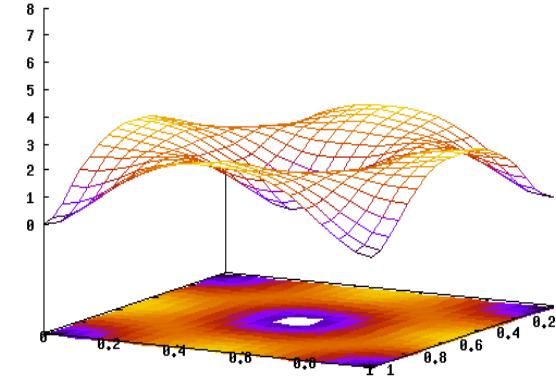
DFT+U



Force Field, Yakub



Force Field, Morelon



DFT+U results in a surface with shape similar to Yakub EP

Electronic degrees of freedom, *i.e.* the f-orbital populations, allow accommodation of lower energy geometric configurations.

Will be demonstrated for the {110} surface